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grant of the state	Application No.	Applicant(s)	
Notice of Allowability	10/815,473	COSNIER ET AL.	
	Examiner	Art Unit	
	Laura M. Schillinger	2813	
The MAILING DATE of this communication appears on the cover sheet with the correspondence address All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS. This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.			
1. This communication is responsive to <u>2/13/06</u> .			
2. The allowed claim(s) is/are 12-18.			
 Acknowledgment is made of a claim for foreign priority unapplicant has THREE-MONTH PERIOD IS NOT EXTENDABLE. Acknowledgment is made of a claim for foreign priority unapplicant has a claim for foreign priority unapplicant for is made of a claim for foreign priority unapplicant for is made of the priority documents have a claim for its material foreign for the priority documents have a claim for its material foreign for its material foreign for its material foreign priority unapplicant for its material foreign for its material for its material foreign for its material foreign for its material for its material foreign for its material for its material foreign for its material for its material foreign foreign for its material for its material foreign foreign for its material foreign for i	been received. been received in Application No cuments have been received in this i	national stage applica	
4. A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.			
 5. CORRECTED DRAWINGS (as "replacement sheets") must be submitted. (a) including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached 1) hereto or 2) to Paper No./Mail Date (b) including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the header according to 37 CFR 1.121(d). 			
6. DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.			
Attachment(s) 1. ☑ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material	5. ☐ Ńotice of Informal P 6. ☐ Interview Summary Paper No./Mail Dat 7. ☐ Examiner's Amendr 8. ☑ Examiner's Stateme	(PTO-413), te ment/Comment	·
	. <u>Ouici</u> .		

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DETAILED ACTION

Allowable Subject Matter

Claims 12-18 are allowed.

The following is an examiner's statement of reasons for allowance:

In reference to claim 12, Dutartre teaches a semiconductor device comprising:

a substrate (Col.2, lines: 25-30);

a gate dielectric (Fig.1 (3)) deposited on the substrate Col.2, lines: 25-30); and

a gate (2) formed on top of a first layer comprising:

a $Si_{1-x}Ge_x$ first layer formed directly on the gate dielectric, where 0.5 < x < 1 (Fig. 2 (11));

and,

a $Si_{1-y}Ge_y$ second layer, formed on top of the $Si_{1-x}Ge_x$ first layer $0 \le y \le 1$ (Fig.2 (12)).

However, Dutartre fails to teach forming the gate on top of a Si_{1-x}Ge_x first layer and also fails to teach that the gate dielectric is made of a high dielectric permittivity material.

Fitzgerald ('735) teaches to form a channel region made of a Si_{1-x}Ge_x first layer (with a gate electrode formed on top of it) [Fig.3] and also teaches that a gate oxide could instead be a high-k dielectric (Col.7, lines: 15-25).

Although it would be obvious to one of ordinary skill in the art at the time the invention was made to modify Dutartre to further include a high-k dielectric rather than an oxide as taught by

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Fitzgerald, the Examiner could find no motivation to modify Dutartre and Fitzgerald to include a Si_{1-x}Ge_x layer underneath a gate which comprised a Si_{1-x}Ge_x and Si_{1-y}Ge_y. Consequently claim 12 contains allowable subject matter. Claims 13-18 depend from allowed claim 12 and act only to further narrow the allowable subject matter therefore all claims are in condition for allowance.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee.

Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Laura M. Schillinger whose telephone number is (571) 272-1697. The examiner can normally be reached on M-T, R-F 7:00-5:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl W. Whitehead, Jr. can be reached on (571) 272-1702. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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06/05/06

Laura M Schillinger Primary Examiner Art Unit 2813